

## INVESTIGATION OF LUMINESCENCE AND PHOTOCONDUCTIVITY SPECTRA OF Se-As CHALCOGENIDE GLASS-LIKE SEMICONDUCTOR SYSTEM DOPED BY EuF<sub>3</sub>

S.N. GARIBOVA<sup>1,2</sup>, S.I. MEKHTIYEVA<sup>1</sup>, M.A. RAMAZANOV<sup>3</sup>

<sup>1</sup>*G.M. Abdullayev Institute of Physics of NASA, Azerbaijan  
AZ-1143, Baku, H. Javid ave., 131*

<sup>2</sup>*Khazar University 41 Mehseti Str., AZ-1096, Baku, Azerbaijan*

<sup>3</sup>*Baku State University, AZ-1148, Z. Khalilov str., 23, Baku, Azerbaijan*

By investigation of the luminescence spectra and the photocurrent spectral distribution of the Se<sub>95</sub>As<sub>5</sub> and Se<sub>95</sub>As<sub>5</sub> (EuF<sub>3</sub>)<sub>x</sub> ( $x = 0.01-1$  at. %) film samples have been shown that the EuF<sub>3</sub> impurity changes the concentration of charged states nonmonotonically. It was established that influence of the EuF<sub>3</sub> impurity on a luminescence and photoconductivity spectra of the Se-As chalcogenide glass-like semiconductor system have been explained within of the charged intrinsic D<sup>-</sup> and D<sup>+</sup> defects model. It was shown that the participation of EuF<sub>3</sub> in Se<sub>95</sub>As<sub>5</sub> leads to an increase in the transparency of the material as a result of a shift in the absorption edge toward shorter wavelengths and photo enlightenment of the material was observed and large number of the impurity result in radiative recombination.

**Keywords:** Chalcogenides, semiconductors, luminescence, impurity, photoconductivity.

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### INTRODUCTION

The use of EuF<sub>3</sub> in the Se-As chalcogenide glass-like semiconductor system as an impurity is due to the fact that the impurity creates additional levels associated with 4f states, which allows controlling the concentration of intrinsic charged defects [1, 2]. Investigations of recording medium based on chalcogenide glass-like semiconductor materials show that under the influence of electromagnetic radiation (laser beam, electron beam, incoherent radiation from ordinary light sources), as a result of complex physicochemical processes occurring in the material, the medium changes its basic optical properties: the position of the optical absorption edge, transmittance, reflection, refraction. Usually, the edge of the absorption band in such irradiated materials as As-S, As-Se and Ge-As-Te shifts toward long waves, photodarkening occurs [3, 4]. Investigation results of the optical and electrical properties of chalcogenide glass-like semiconductors (CGS) make it possible to control the concentration of intrinsic charged defects by doping with an impurity capable of forming charged states [5, 6]. It was proved that during the luminescence of the CGS, the states associated with these defects participate. Based on the results of the study, the recombination centers are due not to impurities, but to free bonds. The luminescence intensity increases significantly when As and Te added to Se, which lead to an increase in the number of free bonds: As branches, and Te shortens the chains of Se [7]. In the case of very thin samples (< 15 μm), the maximum of the excitation spectra and the high-energy region shift with a change in the thickness of the samples, and according to Bishop and Mitchell [8], the process of surface recombination is responsible for the decay of the excitation spectrum in the high-energy region. Another explanation for the recession in the excitation spectrum in the high-energy region according to Street [9] is not due to surface recombination, but to the dependence of the quantum yield on the excitation energy. These studies pursue the creation of a new class of active media of

optoelectronic devices operating in the infrared region of the spectrum with different pump variants. To achieve this goal, research is also contributing to the relationship between the composition of the material and the nature of the centers responsible for radiative recombination and the quantum luminescence yield.

### EXPERIMENTAL AND SAMPLE PREPARATION

The synthesis of the Se-As system with the EuF<sub>3</sub> impurity was performed by alloying corresponding amounts of ultra-pure-grade chemical elements in evacuated quartz cells at temperatures above 1173 K in a rotating furnace followed by cooling under turned-off-furnace conditions. The impurity was introduced during the synthesis, its concentration was within 0.001 – 1 at. %. Film samples were fabricated by thermal evaporation in a vacuum chamber with a residual pressure of 10<sup>-5</sup> Torr. onto glass substrates in the VUP-2 installation. The thickness of the investigated films is 3 μm. Al or ITO was used as a conductive surface for measuring the photocurrent. Samples for measuring photoconductivity were a “sandwich” structures. The luminescence spectra of film samples of the Se-As system with an EuF<sub>3</sub> impurity are recorded on a Cary Eclipse spectrofluorimeter. As a source of electromagnetic radiation, a xenon lamp (A = 1000 nm) have been used. To measure the electrical conductivity and photocurrent, the Keithley 6487 automated installation was used as the current amplifier. All measurements were taken at room temperature.

### RESULTS AND DISCUSSION

Fig. 1 shows the luminescence spectra of film samples of the Se<sub>95</sub>As<sub>5</sub> and Se<sub>95</sub>As<sub>5</sub> (EuF<sub>3</sub>)<sub>x</sub> ( $x = 0.25-1$  at.%) compositions. The film of the Se-As glass upon irradiation with a xenon lamp becomes transparent due to a shift in the absorption edge towards shorter wavelengths.

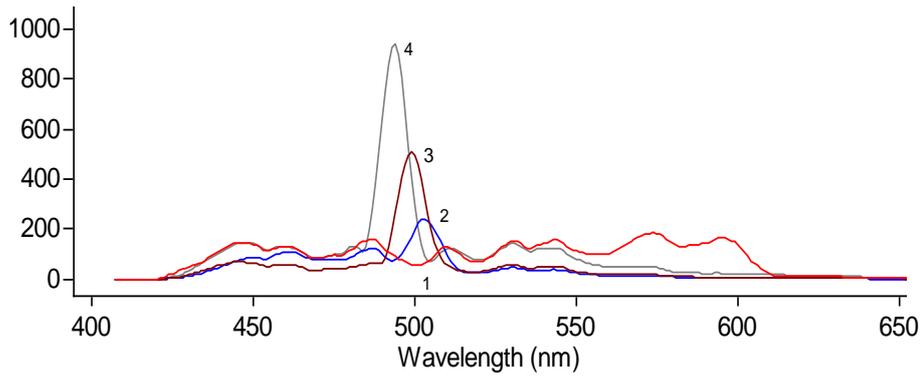


Fig. 1. The luminescence spectra of a Se-As film with an  $\text{EuF}_3$  impurity ( $\lambda_{\text{ex}}=255$  nm,  $T=300\text{K}$ ):  
 1- $\text{Se}_{95}\text{As}_5$ , 2-  $\text{Se}_{95}\text{As}_5(\text{EuF}_3)_{0,5}$ , 3-  $\text{Se}_{95}\text{As}_5(\text{EuF}_3)_{0,25}$ , 4-  $\text{Se}_{95}\text{As}_5(\text{EuF}_3)_1$

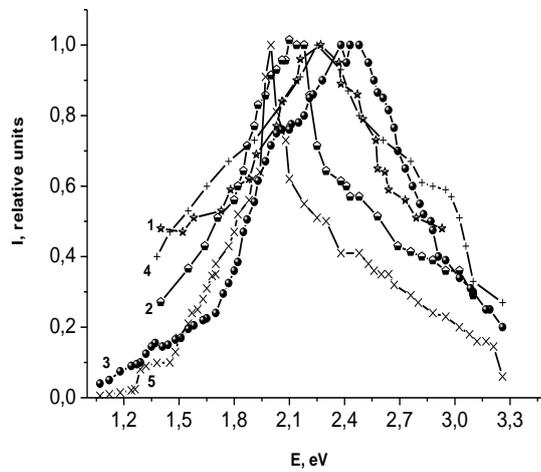


Fig. 2. The spectral distribution of the steady-state photocurrent of the composition  $\text{Se}_{95}\text{As}_5$  with the  $\text{EuF}_3$  impurity ( $T = 300\text{K}$ ): 1 -  $\text{Se}_{95}\text{As}_5$ , 2 -  $\text{Se}_{95}\text{As}_5(\text{EuF}_3)_{0,01}$ , 3 -  $\text{Se}_{95}\text{As}_5(\text{EuF}_3)_{0,05}$ , 4 -  $\text{Se}_{95}\text{As}_5(\text{EuF}_3)_{0,50}$ , 5 -  $\text{Se}_{95}\text{As}_5(\text{EuF}_3)_{1,00}$

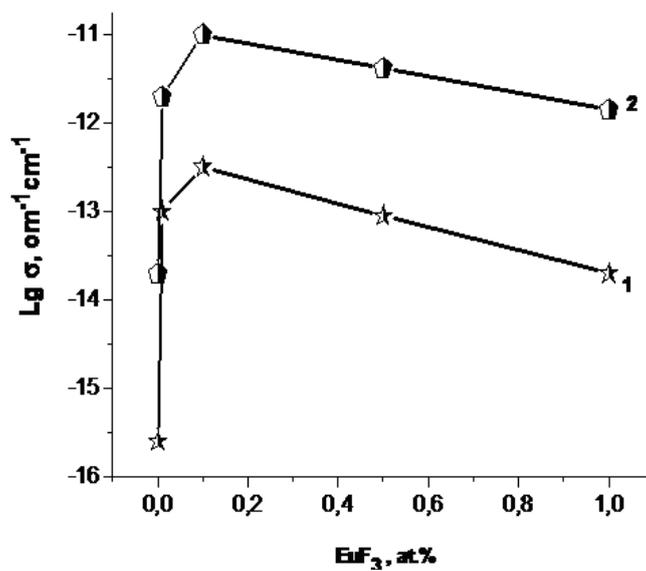


Fig. 3. Dependence of dark conductivity (curve 1) and photoconductivity (curve 2) of  $\text{Se}_{95}\text{As}_5$  on concentration of  $\text{EuF}_3$  impurity: 1- in the dark, 2-under illumination

Table 1.  
Energy position of acceptor - and donor - like centers in  $\text{Se}_{95}\text{As}_5$  with  $\text{EuF}_3$  impurities.

$\text{EuF}_3$ , at. %	$E_A - E_V$ , eV	$E_G$ , eV	$E_D - E_V$ , eV
0	0.6	0.98	1.18
0.01	0.62	0.96	1.2
0.05	0.62	0.96	1.2
0.1	0.64	0.95	1.2
0.5	0.64	0.96	1.2
1	0.66	0.97	1.22

As can be seen from this figure, the participation of  $\text{EuF}_3$  in  $\text{Se}_{95}\text{As}_5$  results in photo enlightenment of the investigated material. The direction of the shift of the absorption edge depends on the parameters of the radiation source and the structural state of the glassy material. Influencing the concentration of charged centers,  $\text{EuF}_3$  at high doses promotes radiative recombination. From the spectral distribution of the steady-state photocurrent (Fig. 2), we can see how the impurity weakens the features near the energies 1.6 and 1.8 eV at low concentrations, which indicates a decrease in the concentration of charged centers. At high impurity concentrations, there is a noticeable enhancement near 1.8 eV, contributing to an increase in  $D^-$  and a decrease in  $D^+$  centers.

The impurity  $\text{EuF}_3$  strongly influences the value of dark conductivity (DC), photoconductivity (PC), and the spectral distribution of the photocurrent, as well as the concentration of intrinsic charged defects. Small concentrations of  $\text{EuF}_3$  lead to a strong increase in both DC and PC (Fig. 3), which is explained by a decrease in the concentration of local states trapping free carriers, which is also associated with charged defects.

From the data on the photoconductivity, some parameters of the charged defects model were calculated, in particular, the value of the effective correlation energy  $U_{ef}$ , which is 0.6 eV and the energy of the polaron relaxation  $W^+$  and  $W^-$ , 0.4 and 0.45 eV, respectively. From the data on the temperature dependence of the dark conductivity and photoconductivity, we have estimated the positions of the recombination levels  $E_d$  and  $E_a$  with respect to the edge of the valence band, and also the

activation energy of the dark conductivity, i.e. position of the Fermi level ( $E_f$ ) relative to the edge of the valence band ( $E_V$ ), the results of which are presented in the table 1 below.

## CONSLUSIONS

Thin films production of Se-As system with  $\text{EuF}_3$  impurity follows the creation of a new class of active medium - optoelectronic devices operating in the infrared region of the spectra. Investigations of the chalcogenide glasses structural features with an impurity of rare-earth elements trace the relationship between the materials composition and the centers nature responsible for radiative recombination and the luminescence quantum yield. The participation of the  $\text{EuF}_3$  impurity in Se-As chalcogenide glass-like semiconductor system creates additional levels associated with the 4f states, which allows control of the intrinsic charged defects concentration. The luminescence spectra show that the films  $\text{Se}_{95}\text{As}_5$  and  $\text{Se}_{95}\text{As}_5(\text{EuF}_3)_x$  become transparent under the influence of electromagnetic radiation, and this is explained by the shift of the absorption edge toward shorter wavelengths. The impurity of  $\text{EuF}_3$  in  $\text{Se}_{95}\text{As}_5$  leads to photo enlightenment of the test material, and large amount of  $\text{EuF}_3$  contribute to radiative recombination. A similar phenomenon can also be observed in the spectral distribution of a steady-state photocurrent. The effect of the  $\text{EuF}_3$  impurity in large amount occurs within the framework of the charged defects model. Investigation of the luminescence spectrum and the photocurrent spectral distribution of the of  $\text{Se}_{95}\text{As}_5$  and  $\text{Se}_{95}\text{As}_5(\text{EuF}_3)_x$  ( $x = 0.01-1$  at.%) film samples shows that the  $\text{EuF}_3$  impurity changes the concentration of charged states nonmonotonically. The impurity here is mainly manifested in the form of  $\text{Eu}^{3+}$  ions, as a result of which the concentration of  $D^-$  centers increases, and the  $D^+$  centers decrease. From the data on photoconductivity, the parameters of the charged defects model, such as the value of the effective correlation energy  $U_{eff}$  (0.6 eV) and the energy of the polaron relaxation  $W^+$  (0.4 eV),  $W^-$  (0.45 eV) are calculated.

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